



High Performance InGaAs p-i-n Photodiode

'FC' Active Device Mount

13PD75-FC

The 13PD75-FC, an InGaAs photodiode with a 75 μ m-diameter photosensitive region packaged in a TO-46 header and aligned in an FC active device mount, is intended for high speed and low noise applications. Planar semiconductor design and dielectric passivation provide superior low noise performance. Reliability is assured by hermetic sealing and a 100% purge burn-in (200°C, 15 hours, $V_r = 20V$).

Features

Planar Structure
Dielectric Passivation
100% Purge Burn-In
High Responsivity

Device Characteristics:						
Parameters	Test Conditions	Min	Typ	Max	Units	
Operating Voltage	-	-	-	-20	Volts	
Dark Current	-5V	-	0.2	2	nA	
Capacitance	-5V	-	0.70	0.9	pF	
Responsivity	1300nm	0.65	0.8	-	A/W	
Rise/Fall	-	-	-	0.5	ns	
Frequency Response	(-3dB)	-	1.5	-	GHz	
Absolute Maximum Ratings						
Reverse Voltage						30 Volts
Forward Current						5 mA
Reverse Current						5 mA
Operating Temperature						-40°C to + 85°C
Storage Temperature						-40°C to + 85°C
Soldering Temperature						250°C